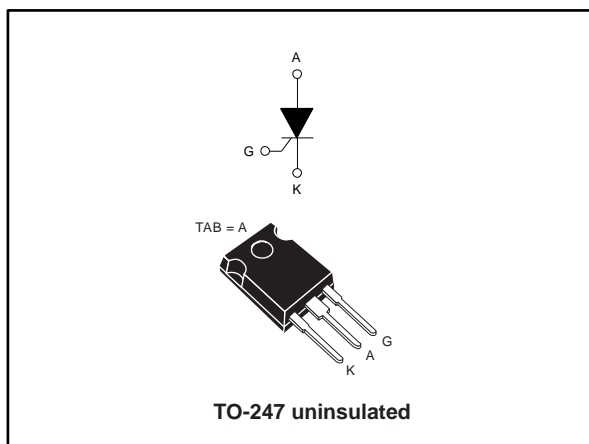


## 30 A - 1200 V automotive grade SCR Thyristor

Datasheet - production data




### Description

This device is an automotive grade SCR Thyristor designed for applications such as automotive and stationary battery chargers.

This SCR Thyristor, rated for a 30 A RMS power switching, offers superior performances in peak voltage robustness up to 1400 V and surge current handling up to 300 A sine wave pulse. Its key features allow the design of functions such as a 42 A RMS AC switch (dual back-to-back SCRs) and a 38 A av. AC-DC controlled rectifier bridge.

Available in through-hole TO-247 package, this power package allows a thermal operation up to 30 A RMS with a higher case temperature of 126 °C.

### Features

- AEC-Q101 qualified 
- High junction temperature:  $T_j = 150\text{ °C}$
- AC off state voltage:  $\pm 1200\text{ V}$
- Nominal on-state current: 30 A<sub>RMS</sub>
- High noise immunity: 1000 V/ $\mu\text{s}$
- Max. gate triggering current: 50 mA
- Ecopack®2 compliant component

### Applications

- Automotive applications: on board and off board battery charger
- Renewable energy inverters
- Solid state relay
- 3-Phase heating or motor soft start control
- UPS (uninterruptible power supply)
- Bypass SSR / hybrid relay
- Inrush current limiter in battery charger
- AC-DC voltage controlled rectifier
- Industrial welding systems

Table 1: Device summary

Symbol	Value
$I_{T(RMS)}$	30 A
$V_{DRM}/V_{RRM}$	1200 V
$V_{DSM}/V_{RSM}$	1400 V
$I_{GT}$	50 mA
$T_j$	150 °C

# 1 Characteristics

**Table 2: Absolute ratings (limiting values)**

Symbol	Parameter		Value	Unit
$I_{T(RMS)}$	RMS on-state current (180 ° conduction angle)		30	A
$I_{T(AV)}$	Average on-state current (180 ° conduction angle)		19	A
$I_{TSM}^{(1)}$	Non repetitive surge peak on-state current	$t_p = 8.3 \text{ ms}$	330	A
		$t_p = 10 \text{ ms}$	300	
$V_{DRM} / V_{RRM}$	Repetitive off-state voltage (50-60 Hz)		1200	V
$di/dt$	Critical rate of rise of on-state current $I_G = 2 \times I_{GT}$ , $t_r \leq 100 \text{ ns}$	$f = 50 \text{ Hz}$	200	A/ $\mu\text{s}$
$I_{GM}$	Peak forward gate current	$t_p = 20 \text{ }\mu\text{s}$	8	A
$P_{G(AV)}$	Average gate power dissipation		1	W
$T_{stg}$	Storage junction temperature range		-40 to +150	°C
$T_j$	Operating junction temperature		-40 to +150	°C

**Notes:**

<sup>(1)</sup>ST recommend  $I^2t$  value for fusing = 450 A<sup>2</sup>s for  $T_j = 25 \text{ }^\circ\text{C}$  and  $t_p = 10 \text{ ms}$

**Table 3: Electrical characteristics ( $T_j = 25 \text{ }^\circ\text{C}$  unless otherwise specified)**

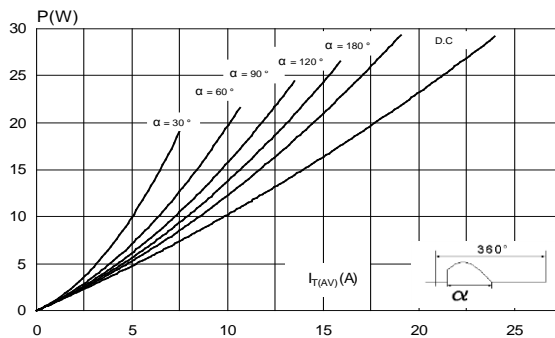
Symbol	Test Conditions		Value	Unit
$I_{GT}$	$V_D = 12 \text{ V}$ , $R_L = 33 \text{ }\Omega$	Min.	10	mA
		Max.	50	
$V_{GT}$	$V_D = 12 \text{ V}$ , $R_L = 33 \text{ }\Omega$		Max. 1.3	V
$V_{GD}$	$V_D = 2/3 \times V_{DRM}$ , $R_L = 3.3 \text{ k}\Omega$	$T_j = 150 \text{ }^\circ\text{C}$	Min. 0.2	V
$I_H$	$I_T = 500 \text{ mA}$ , gate open		Max. 100	mA
$I_L$	$I_G = 1.2 \times I_{GT}$		Max. 125	mA
$t_{gt}$	$I_T = 60 \text{ A}$ , $V_D = 2/3 \times V_{DRM}$ , $I_G = 100 \text{ mA}$ , $di_G/dt = 0.2 \text{ A}/\mu\text{s}$		Typ. 1	$\mu\text{s}$
$dV/dt$	$V_D = 2/3 \times V_{DRM}$ , gate open	$T_j = 150 \text{ }^\circ\text{C}$	Min. 1000	V/ $\mu\text{s}$
$t_q$	$I_T = 20 \text{ A}$ , $di_T/dt = 10 \text{ A}/\mu\text{s}$ , $V_R = 75 \text{ V}$ , $V_D = 2/3 \times V_{DRM}$ , $dV_D/dt = 20 \text{ V}/\mu\text{s}$ , $t_p = 100 \text{ }\mu\text{s}$	$T_j = 150 \text{ }^\circ\text{C}$	Typ. 150	$\mu\text{s}$
$V_{TM}$	$I_{TM} = 60 \text{ A}$ , $t_p = 380 \text{ }\mu\text{s}$		Max. 1.65	V
$V_{TO}$	Threshold voltage	$T_j = 150 \text{ }^\circ\text{C}$	Max. 0.88	V
$R_D$	Dynamic resistance	$T_j = 150 \text{ }^\circ\text{C}$	Max. 14	m $\Omega$
$I_{DRM}/I_{RRM}$	$V_D = V_{DRM}$ , $V_R = V_{RRM}$	$T_j = 25 \text{ }^\circ\text{C}$	Max. 5	$\mu\text{A}$
		$T_j = 125 \text{ }^\circ\text{C}$	Max. 3	mA
		$T_j = 150 \text{ }^\circ\text{C}$	Max. 5	mA
$I_{DSM}/I_{RSM}$	$V_D = V_{DSM}$ , $V_R = V_{RSM}$	$T_j = 25 \text{ }^\circ\text{C}$	Max. 10	$\mu\text{A}$

Table 4: Thermal parameters

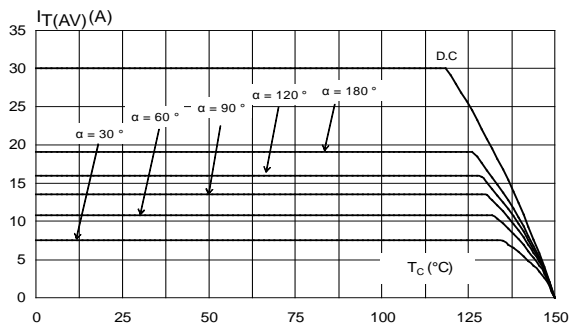
Symbol	Parameter		Value	Unit
$R_{th(j-c)}$	Junction to case (DC, max.)	TO-247	0.8	°C/W
$R_{th(j-a)}$	Junction to ambient (typ.)		50	

## 1.1 Characteristics (curves)

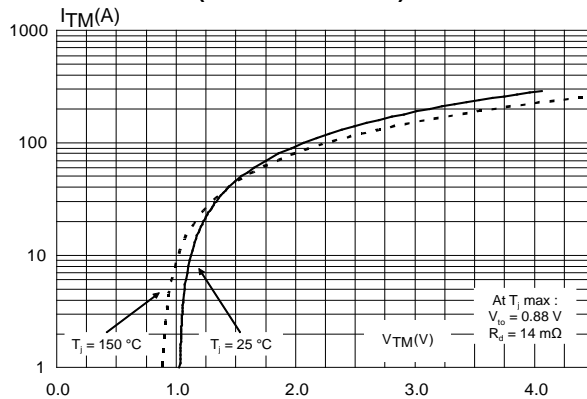
**Figure 1: Maximum average power dissipation versus average on-state current**



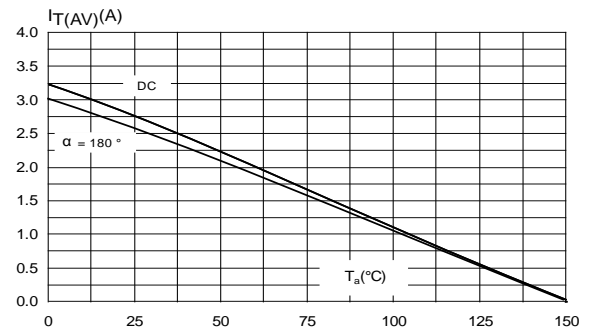
**Figure 2: Average and DC on-state current versus case temperature**



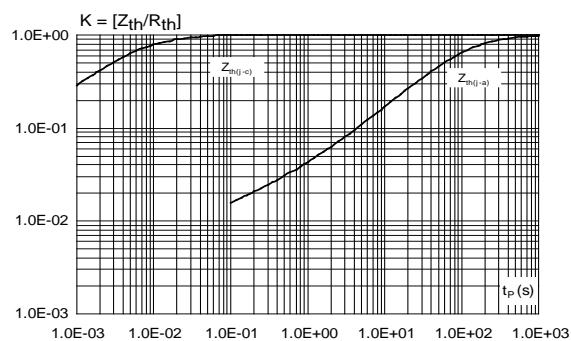
**Figure 3: On-state characteristics (maximum values)**



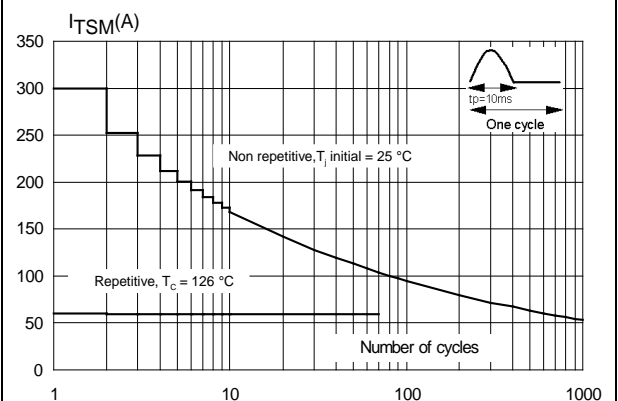
**Figure 4: Average and D.C. on-state current versus ambient temperature**

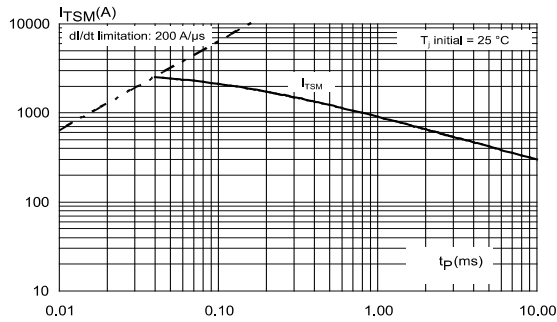
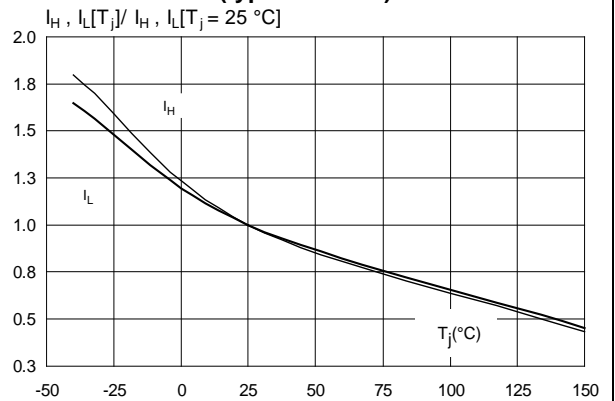
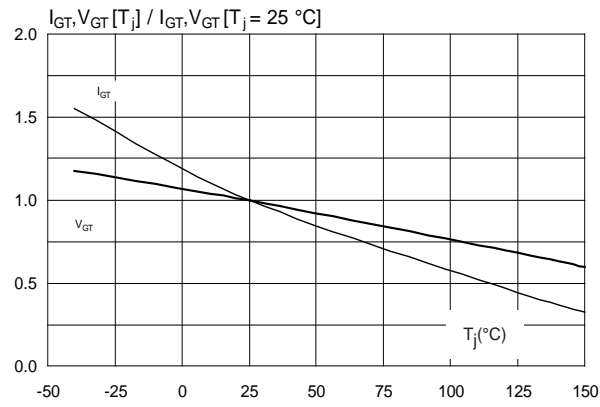
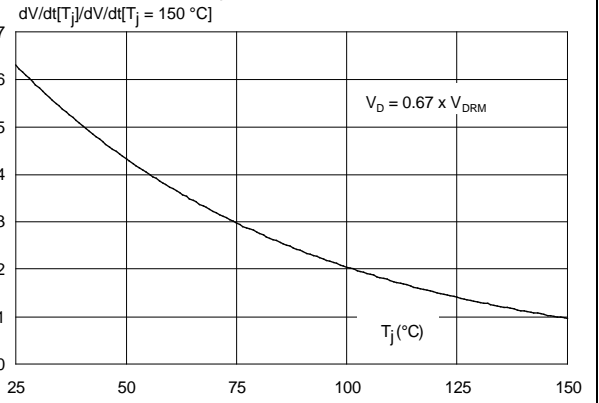
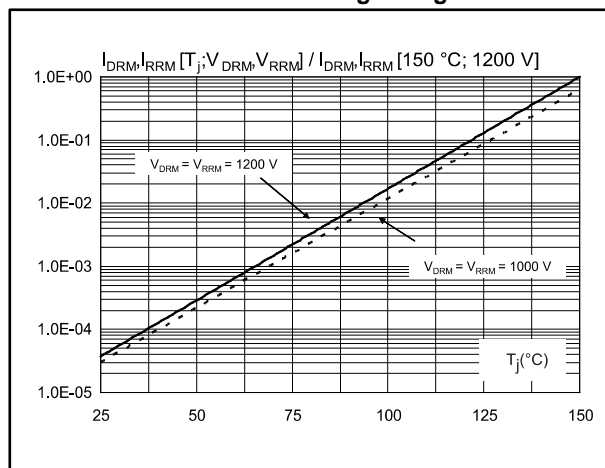


**Figure 5: Relative variation of thermal impedance junction to case and junction to ambient versus pulse duration**



**Figure 6: Surge peak on-state current versus number of cycles**



**Figure 7: Non repetitive surge peak on-state current for a sinusoidal pulse ( $t_p < 10$  ms)****Figure 8: Relative variation of holding and latching current versus junction temperature (typical values)****Figure 9: Relative variation of gate triggering current and voltage versus junction temperature****Figure 10: Relative variation of the static dV/dt immunity versus junction temperature (typical values)****Figure 11: Relative variation of leakage current versus junction temperature for different values of blocking voltage**

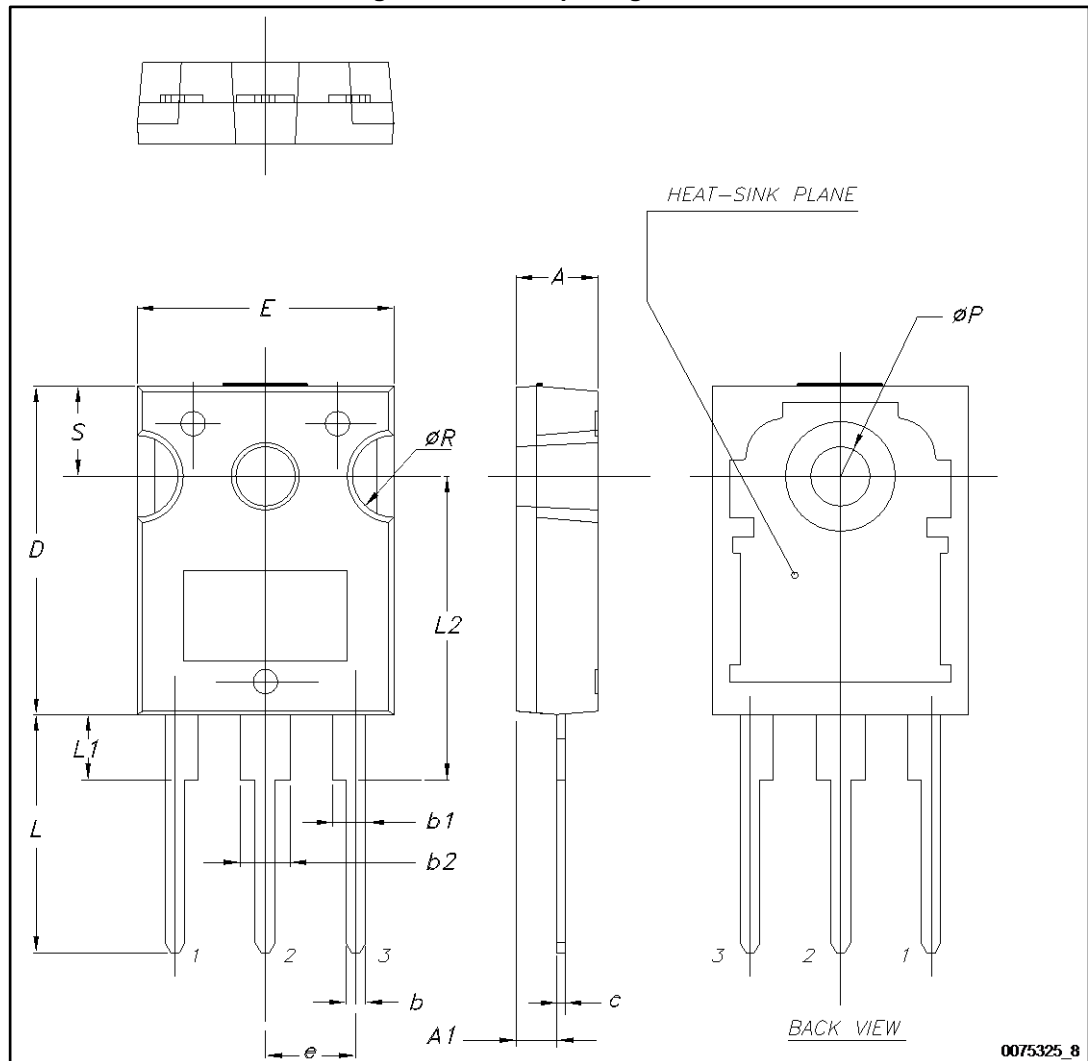
## 2 Package information

In order to meet environmental requirements, ST offers these devices in different grades of ECOPACK® packages, depending on their level of environmental compliance. ECOPACK® specifications, grade definitions and product status are available at: [www.st.com](http://www.st.com). ECOPACK® is an ST trademark.

- Epoxy meets UL 94,V0
- Recommended torque value: 0.8 N·m
- Maximum torque value: 1 N·m

### 2.1 TO-247 package information

Figure 12: TO-247 package outline



0075325\_8

Table 5: TO-247 package mechanical data

Dim.	Dimensions					
	Millimeters			Inches <sup>(1)</sup>		
	Min.	Typ.	Max.	Min.	Typ.	Max.
A	4.85		5.15	0.1909		0.2028
A1	2.20		2.60	0.0866		0.1024
b	1.0		1.40	0.0394		0.0551
b1	2.0		2.40	0.0787		0.0945
b2	3.0		3.40	0.1181		0.1339
c	0.40		0.80	0.0157		0.0315
D <sup>(2)</sup>	19.85		20.15	0.7815		0.7933
E	15.45		15.75	0.6083		0.6201
e	5.30	5.45	5.60	0.2087	0.2146	0.2205
L	14.20		14.80	0.5591		0.5827
L1	3.70		4.30	0.1457		0.1693
L2		18.50			0.7283	
ØP <sup>(3)</sup>	3.55		3.65	0.1398		0.1437
ØR	4.50		5.50	0.1772		0.2165
S	5.30	5.50	5.70	0.2087	0.2165	0.2244

**Notes:**

<sup>(1)</sup>Inch dimensions given only for reference

<sup>(2)</sup>Dimension D plus gate protrusion does not exceed 20.5 mm

<sup>(3)</sup>Resin thickness around the mounting hole is not less than 0.9 mm

### 3 Ordering information

Table 6: Ordering information

Order code	Marking	Package	Weight	Base qty.	Delivery mode
TN3050H-12WY	TN3050H12WY	TO-247	4.4 g	50	Tube

### 4 Revision history

Table 7: Document revision history

Date	Revision	Changes
16-Sep-2016	1	Initial release.
03-Oct-2016	2	Updated <a href="#">Table 4: "Thermal parameters"</a> .

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